

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	8	((("6498092") or ("6309957") or ("5512514") or ("4182636"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/17 11:16
S2	0	S1 and deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and (dielectric or insulat\$4) and coat\$4 and "ion etch\$4" and remov\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/17 11:18
S3	0	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and (dielectric or insulat\$4) and coat\$4 and "ion etch\$4" and remov\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:18
S4	1340	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S5	783	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S6	574	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:19
S7	259	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via and anGLE	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:20
S8	0	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct\$4 and metal and junction and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:23

S9	94	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct\$4 and metal and junction and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:25
S10	4	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct\$4 and metal and junction and contact and magnetic and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:24
S11	40	deposit\$4 and photoresist and pattern\$4 and layer and mask\$4 and protect\$4 and dielectric and coat\$4 and (ion near4 etch) and remov\$4 and relative and via and angle and (wafer or substrate or semiconductor) and conduct\$4 and metal and junction and contact and directional	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:28
S12	11	(semiconductor or substrate or wafer) and conduct\$4 and (deposit near4 photoresist) and mask and protect\$4 and dielectric and "ion etching" and angle and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 11:53
S13	371	(substrate or wafer or semiconductor) and photoresist and pattern and mask\$4 and protect and dielectric and deposit and (ion near4 etch\$4) and angle and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30
S14	351	(substrate or wafer or semiconductor) and photoresist and pattern and mask\$4 and protect and dielectric and deposit and (ion near4 etch\$4) and angle and via and conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30
S15	172	(substrate or wafer or semiconductor) and photoresist and pattern and mask\$4 and protect and dielectric and deposit and (ion near4 etch\$4) and angle and via and conduct\$4 and junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 12:30

S16	74	(substrate or wafer or semiconductor) and photoresist and pattern and mask\$4 and protect and dielectric and deposit and (ion near\$4 etch\$4) and angle and via and conduct\$4 and junction and stack	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 13:11
S17	55	deposit and photoresist and "patterned layer" and mask\$4 and protect and dielectric and "ion etching" and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 14:24
S18	77	photoresist and "patterned layer" and mask\$4 and protect and dielectric and "ion etching" and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:30
S19	0	photoresist and "patterned layer" and mask\$4 and protect and dielectric and "ion etching" and angle and "ion mill\$4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/03/17 15:06
S20	5	photoresist and "patterned layer" and mask\$4 and protect and dielectric and "ion etching" and angle and "ion milling"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:06
S21	1	photoresist and "patterned layer" and mask\$4 and protect and dielectric and "ion etching" and angle and "ion milling" and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 15:07
S22	9003	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:34
S23	8984	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack\$4 and photoresist and "patterned layer" and mask\$4 and dielectric and "ion etching"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:37

S24	8984	"ion milling" or "ion beam etching" and "magnetic tunnel junction" and stack\$4 and photoresist and "patterned layer" and mask\$4 and dielectric and "ion etching" and angle and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:38
S25	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4 and photoresist and "patterned layer" and mask\$4 and dielectric and "ion etching" and angle and protect and deposit\$4 and conduct\$4 and row	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S26	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4 and photoresist and "patterned layer" and mask\$4 and dielectric and "ion etching" and angle and protect and deposit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S27	1	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4 and photoresist and "patterned layer" and mask\$4 and dielectric and "ion etching" and angle and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:39
S28	125	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:40
S29	33	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4 and conduct\$4 and row	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:40
S30	20	("ion milling" or "ion beam etching") and "magnetic tunnel junction" and stack\$4 and conduct\$4 and row and ferromagnetic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 08:40